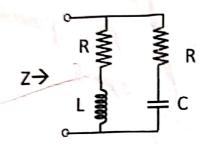
## EE 101: Introduction to Electrical and Electronic Circuits, 2019

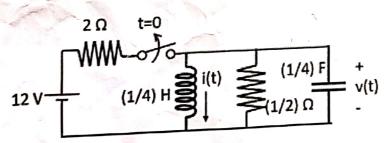
## Midsem

(Show all the steps in the solution properly. Weightage=24%)

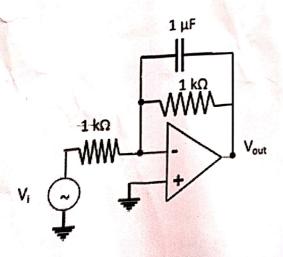
- 1) Consider a piece of Si doped with certain impurities, at 300 K. It was found that the hole concentration is 2.25 X 10<sup>4</sup>/cm<sup>3</sup>. Find out the impurity concentration. The impurity belongs to which group of the periodic table (III or V)? Is it p type or n type semiconductor? Assuming that mobility of electrons is 1300 cm<sup>2</sup>/Vs and holes is 500 cm<sup>2</sup>/Vs, find out the resistivity of doped Si. [4 marks]
- 2) The impedance of the circuit shown below is found to be  $2 \text{ k}\Omega$  (real) at all frequencies. If the value of inductor is 1 mH, find out the values of R and C. [5 marks]



3) For the circuit shown below, the switch opens at t=0. Find out and sketch v(t) and i(t), for t=0 to  $t=\infty$ . [6 marks]



4) Consider the op-amp circuit shown below. Find out the transfer function  $H(\omega)$ . (H=V<sub>out</sub>/V<sub>i</sub>). Plot the real and imaginary parts of H as a function of  $\omega$ . [4 marks]



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5) Consider an op-amp circuit shown below. Assume  $R_1=10~k\Omega$ ,  $R_2=20~k\Omega$ , reference voltage  $V_r=6~V$  and  $V_{CC}=12~V$ . Find out and plot the complete transfer characteristics (i.e.  $V_o$  as a function of  $V_i$ ). [5 marks]

